

IN THE CLAIMS:

Please cancel Claims 1-5, 10, 11, 13-17, 19-22, 32-41, and 43-61 without prejudice or disclaimer of subject matter. (Claims 6-9 and 23-31 were canceled previously).

Please amend Claims 12 and 42, and add Claims 62-69, to read as follows.

1. - 5. (Cancelled)

6. - 9. (Cancelled)

10. - 11. (Cancelled)

12. (Currently Amended) An electron source comprising:

~~a substrate structure according to any one of claims 1 through 5~~
containing Na; and

~~a plurality of electron emission devices a first layer containing SiO₂ as~~
a main component formed directly or indirectly on said substrate;

~~a second layer containing an electron conductive oxide formed~~
directly or indirectly on said substrate; and

~~an electron-emitting material and an electrode connected with said~~
electron-emitting material;

wherein said electron-emitting material and said electrode are
disposed on said first layer or said second layer of the substrate structure.

13. - 17. (Cancelled)

18. (Previously Presented) An image forming apparatus comprising:
an electron source according to claim 12; and
an image forming member to form an image with irradiation of
electrons emitted from the electron source.

19. - 22. (Cancelled)

23. - 31. (Cancelled)

32. - 41. (Cancelled)

42. (Currently Amended) An electron source comprising:
a substrate ~~structure according to any one of claims 32 through 40;~~
and
a first layer containing SiO₂ as a main component formed directly or
indirectly on said substrate;
a second layer containing an electron conductive oxide formed
directly or indirectly on said substrate; and
an electron-emitting material and an electrode connected with said
electron-emitting material;
wherein said electron-emitting material and said electrode are the
electron emission device disposed on said first layer or said second layer of the substrate
structure.

43. - 61. (Cancelled)

62. (New) The electron source according to claim 12, wherein said first layer is formed on said substrate containing Na, and said second layer is formed on the first layer.

63. (New) The electron source according to claim 62, wherein said second layer contains SiO_2 as its ingredient.

64. (New) The electron source according to claim 62, wherein said first layer contains at least one kind of element to be selected from an element group comprising P, B, and Ge.

65. (New) The electron source according to claim 63, wherein said first layer contains at least one kind of element to be selected from an element group comprising P, B, and Ge.

66. (New) The electron source according to claim 42, wherein said first layer is formed on said substrate, and said second layer is formed on the first layer.

67. (New) The electron source according to claim 66, wherein said second layer contains SiO_2 as its ingredient.

68. (New) The electron source according to claim 66, wherein said first layer contains at least one kind of element to be selected from an element group comprising P, B and Ge.

69. (New) The electron source according to claim 67, wherein said first layer contains at least one kind of element to be selected from an element group comprising P, B and Ge.